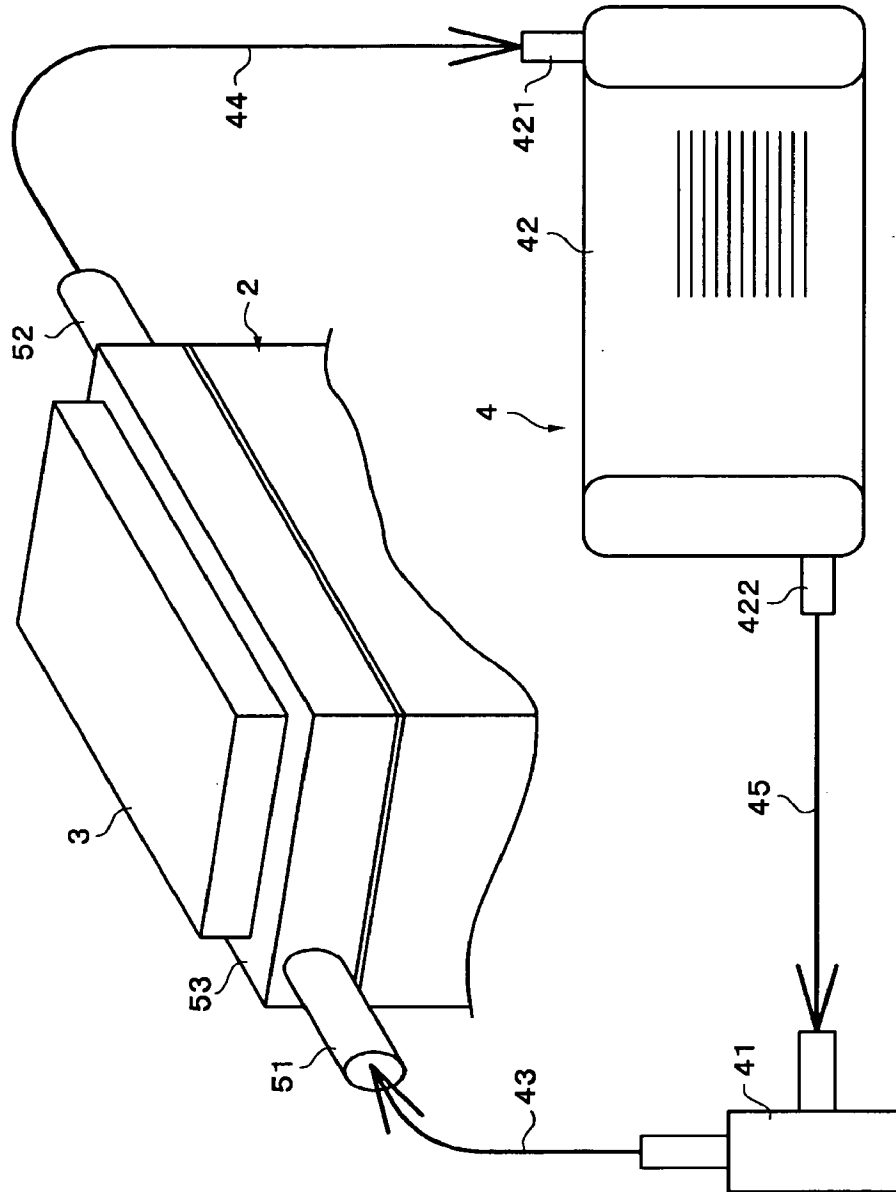


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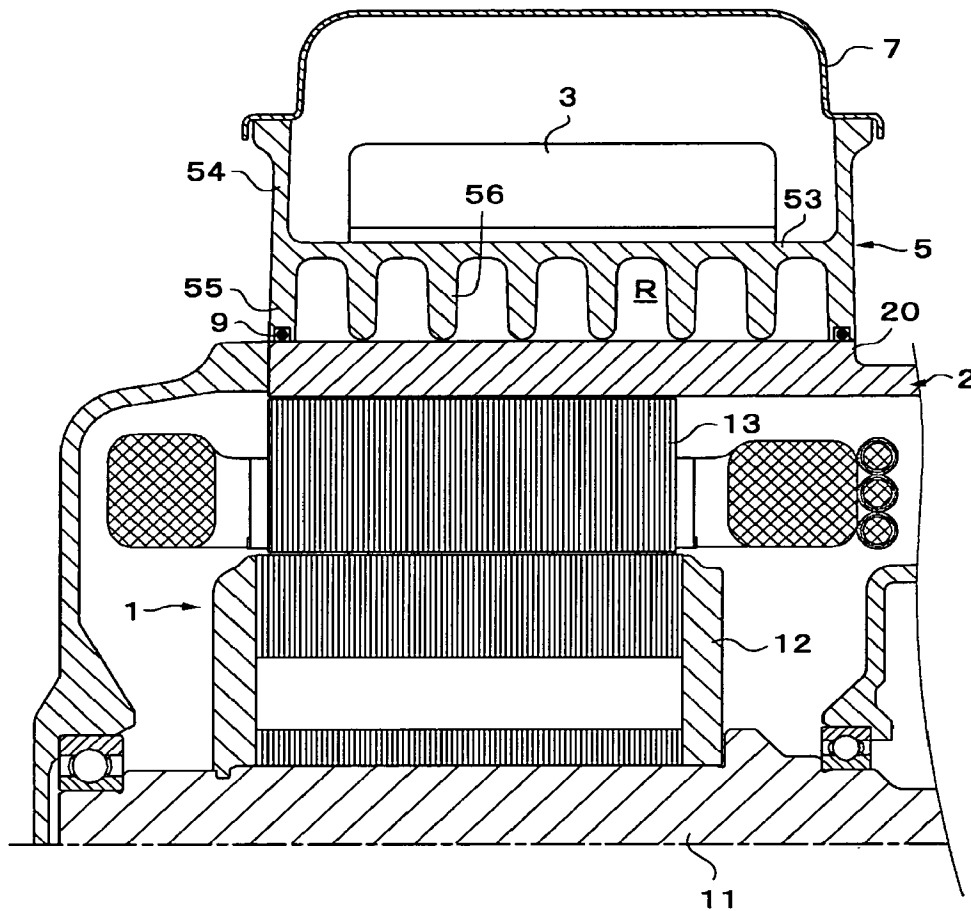
FIG. 1



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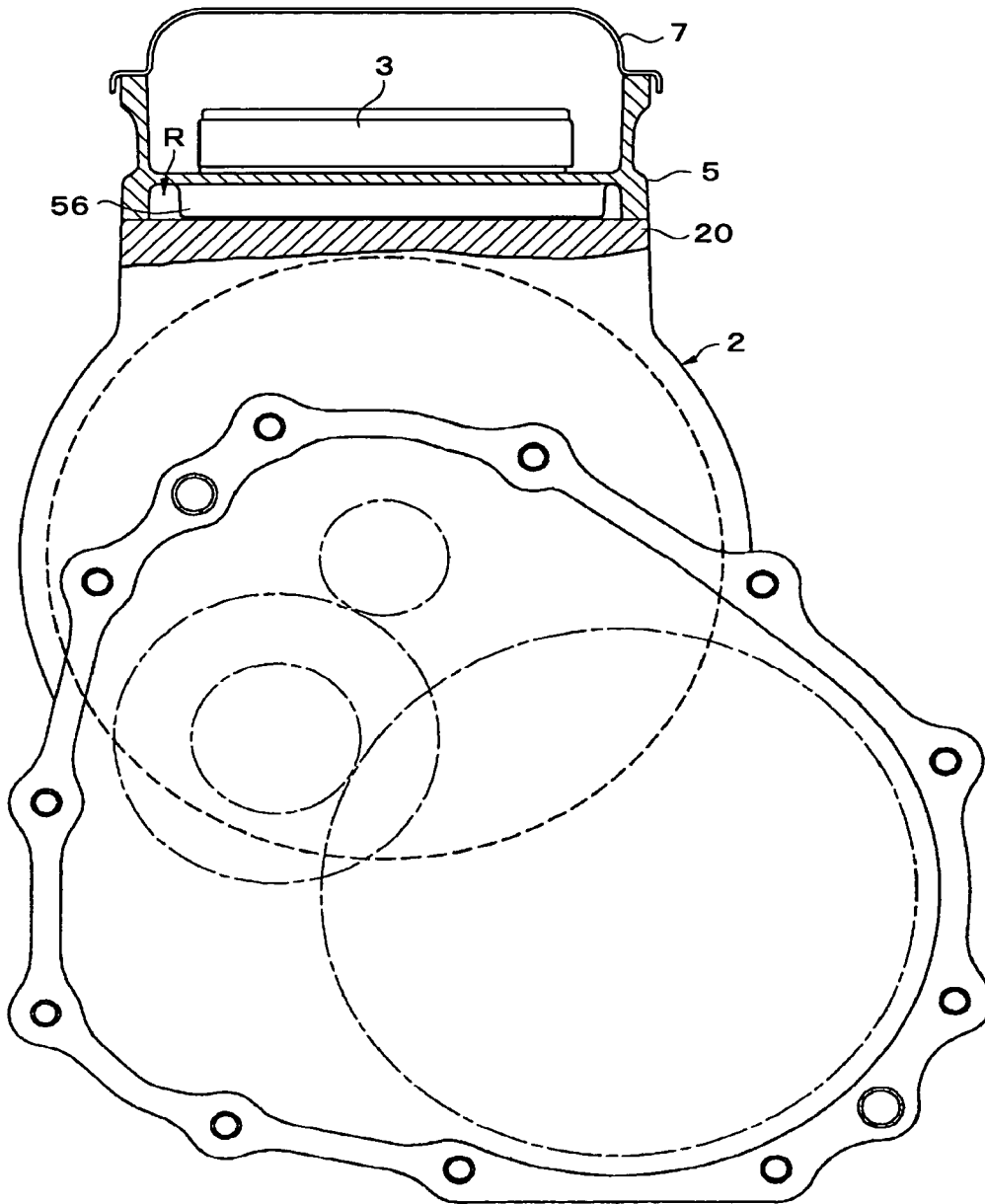
FIG. 2



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FIG. 3



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FIG. 4

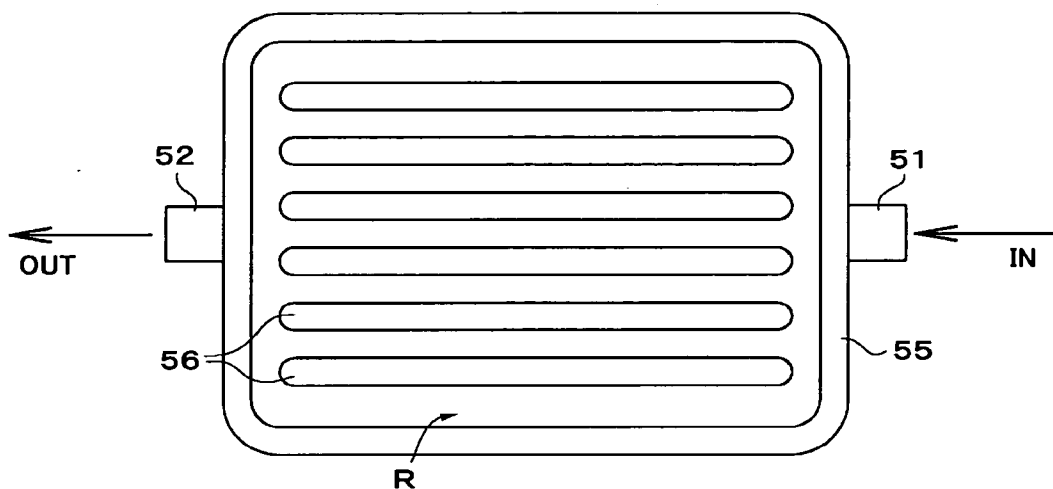
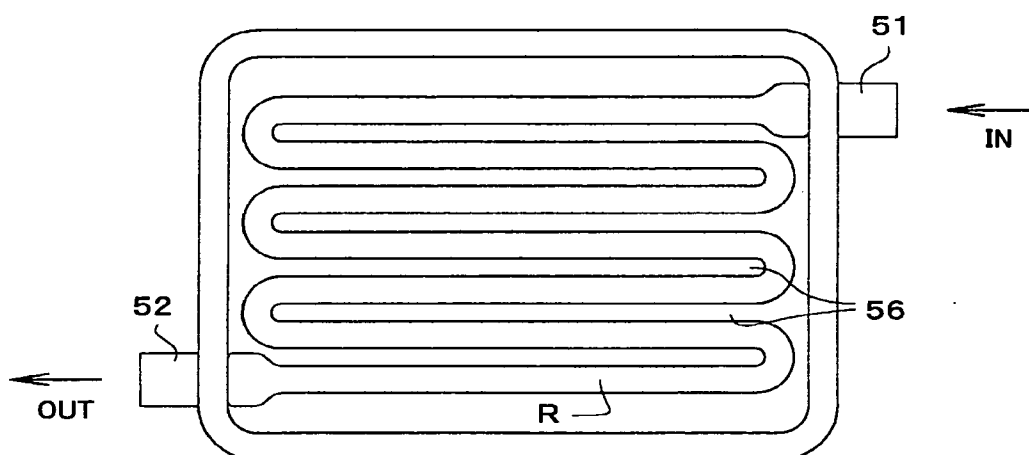


FIG. 5



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FIG. 6

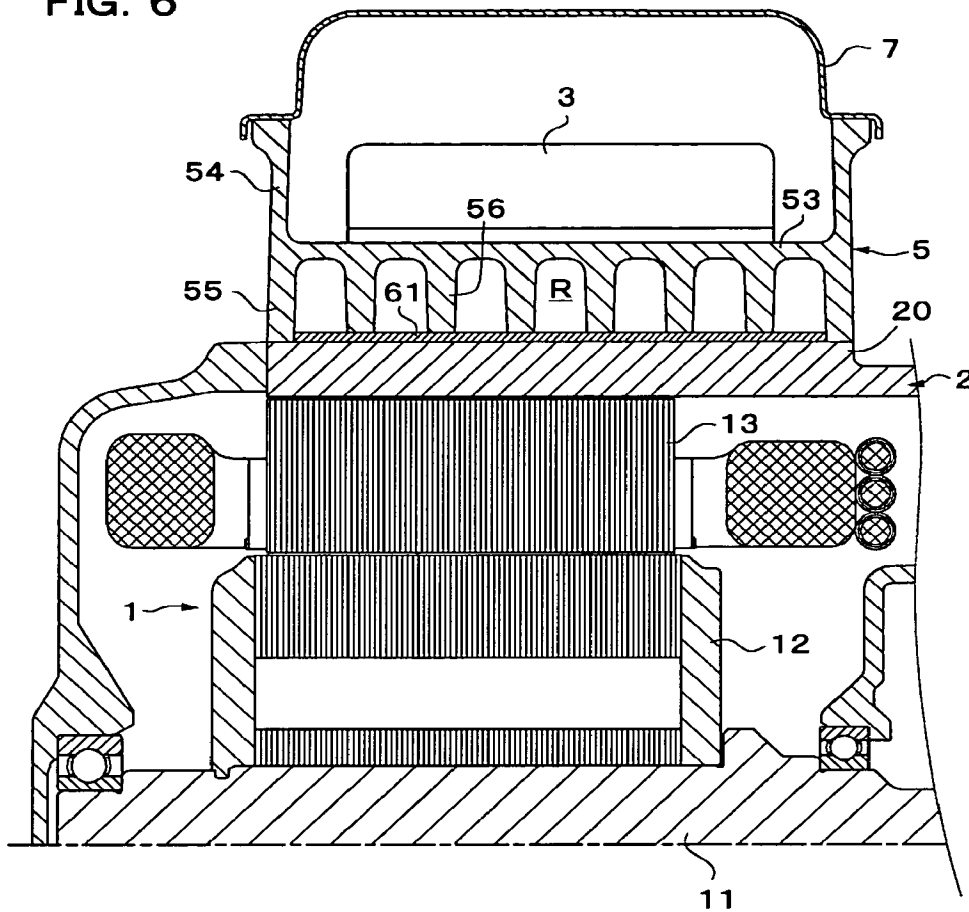
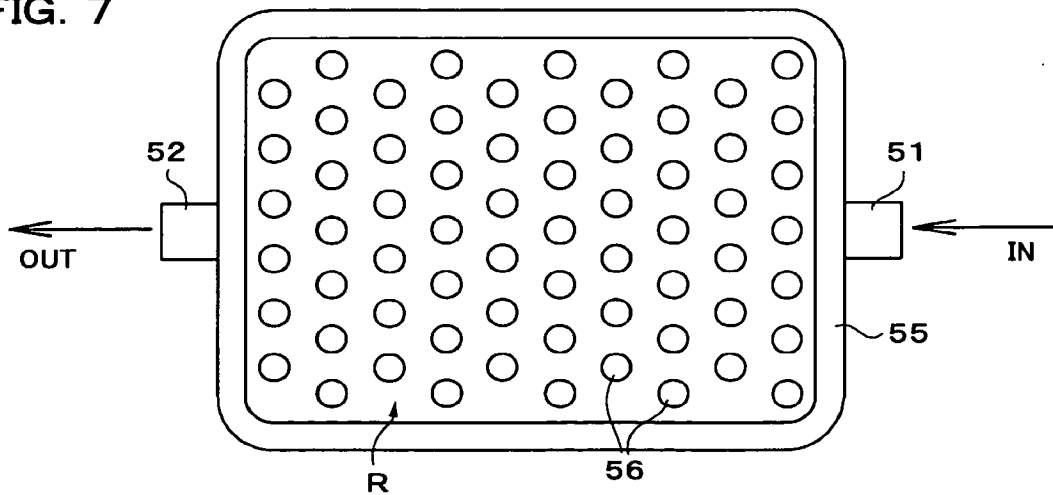


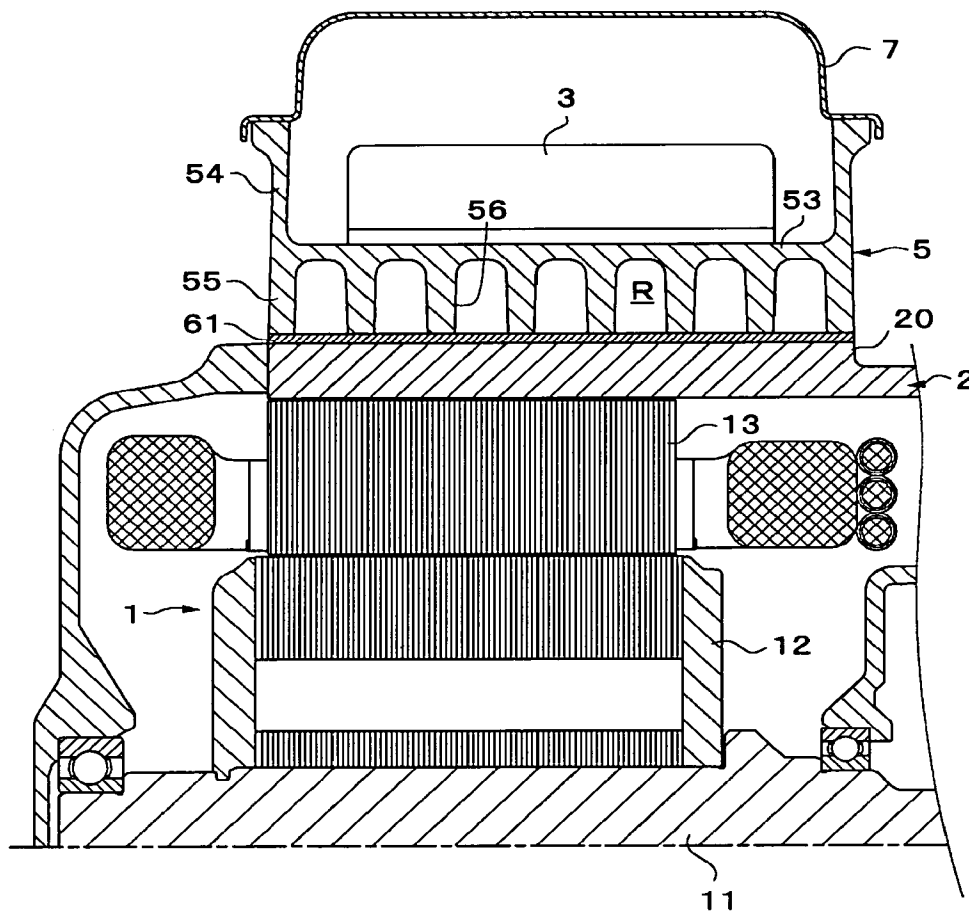
FIG. 7



Appendix A

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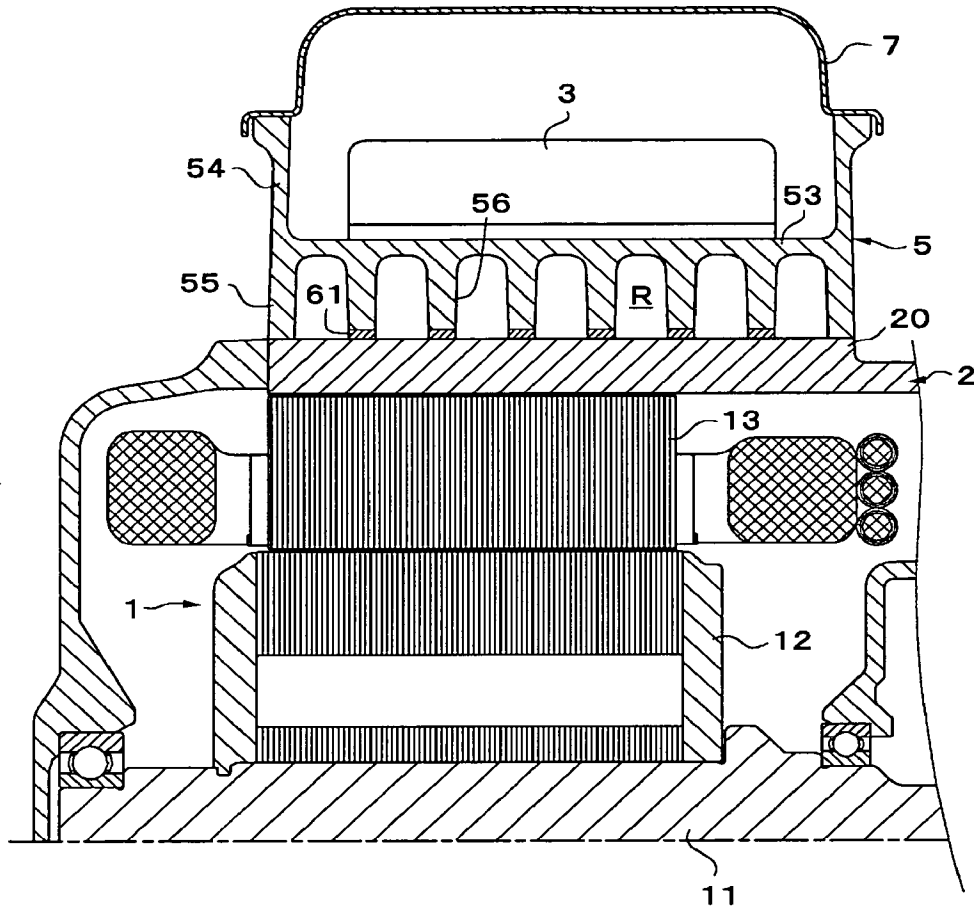
FIG. 8



Appendix A

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FIG. 9



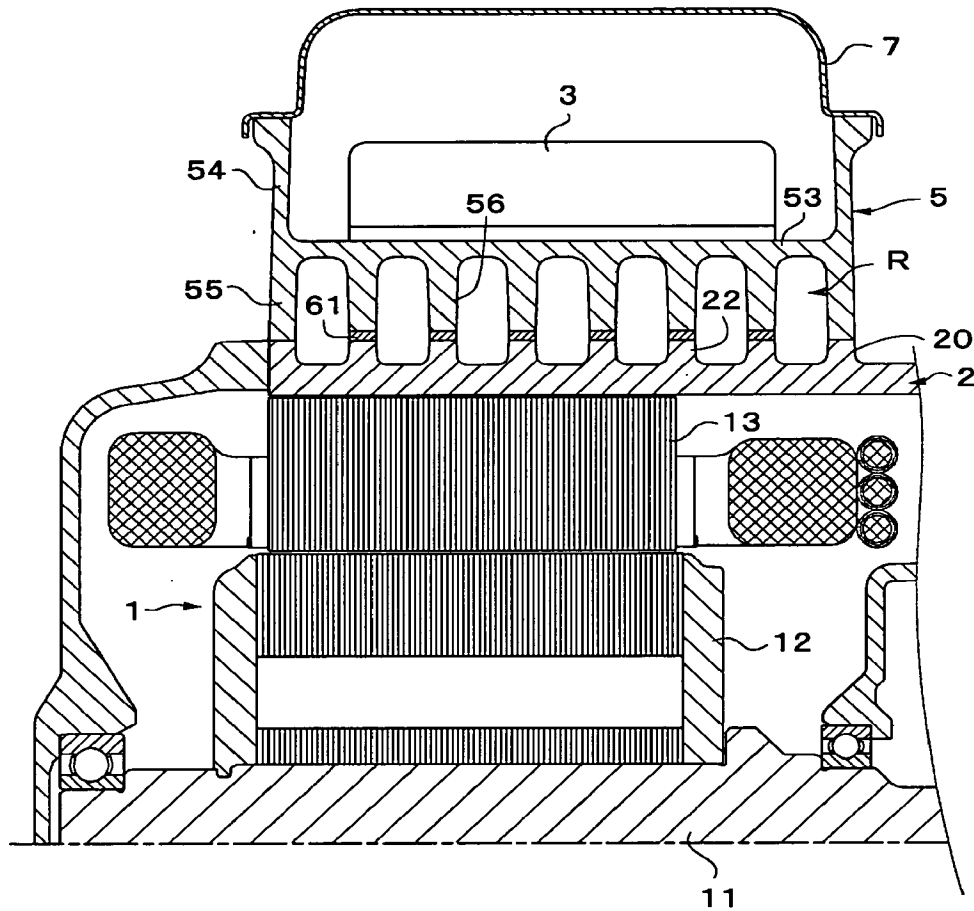
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This cross-sectional view shows a semiconductor device assembly. A substrate 11 is at the base. A central core 12 contains a stack of layers: a bottom layer, a middle layer 13 with vertical hatching, and a top layer. A central opening 1 is formed through the core. On the left and right sides of the core, there are circular features with cross-hatching, each containing three small circles. Above the core, a layer 20 is shown with a series of rectangular protrusions 55. A layer 54 is above this, and a top layer 53 contains a rectangular region 56. A central opening 3 is located within the top layer 53. The entire assembly is enclosed in a housing 7.

Appendix A

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FIG. 11



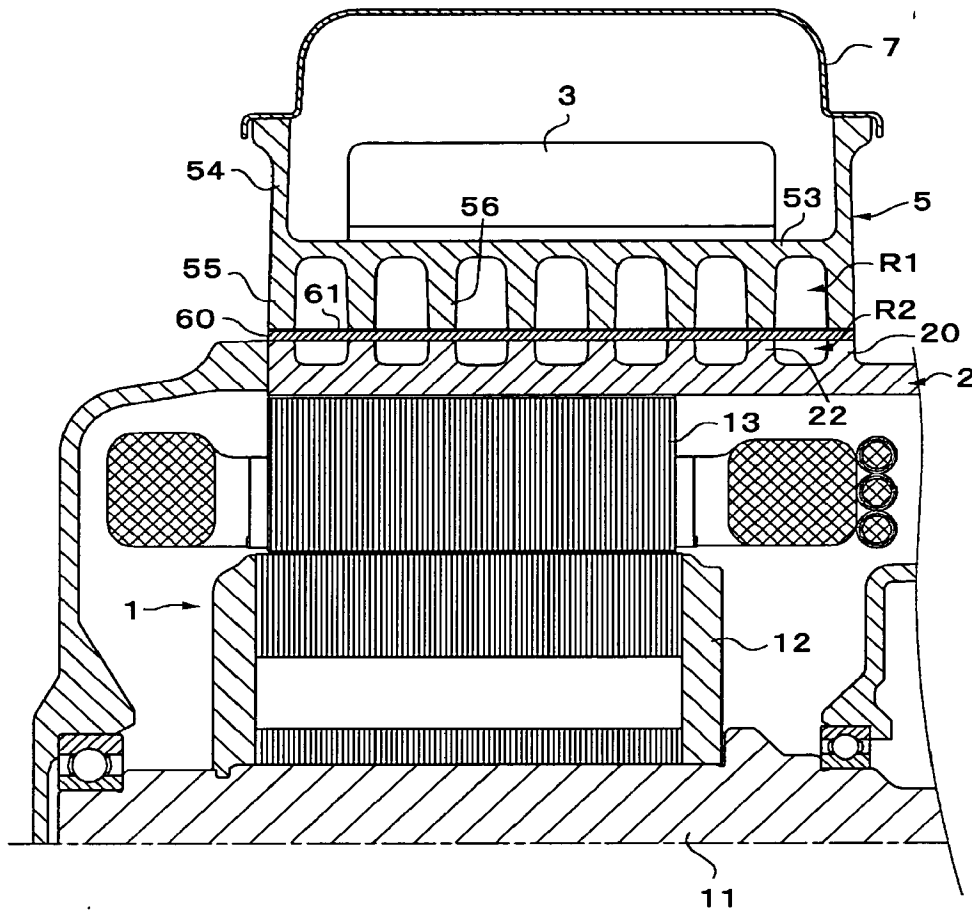
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This cross-sectional view shows a semiconductor device assembly. A substrate 11 is at the base. A central stack includes a layer 12, a thick conductive layer 13, and another layer 12. This stack is flanked by two cross-hatched regions, likely solder bumps or pads. Above the central stack is a layer 20 containing a series of vertical elements 22, which are connected to a horizontal layer 61. Above this is a layer 53 containing a series of vertical elements 56, connected to a horizontal layer 54. The entire assembly is enclosed in a housing 7, with a top layer 3 and a side layer 5. A reference numeral R is also present.

Appendix A

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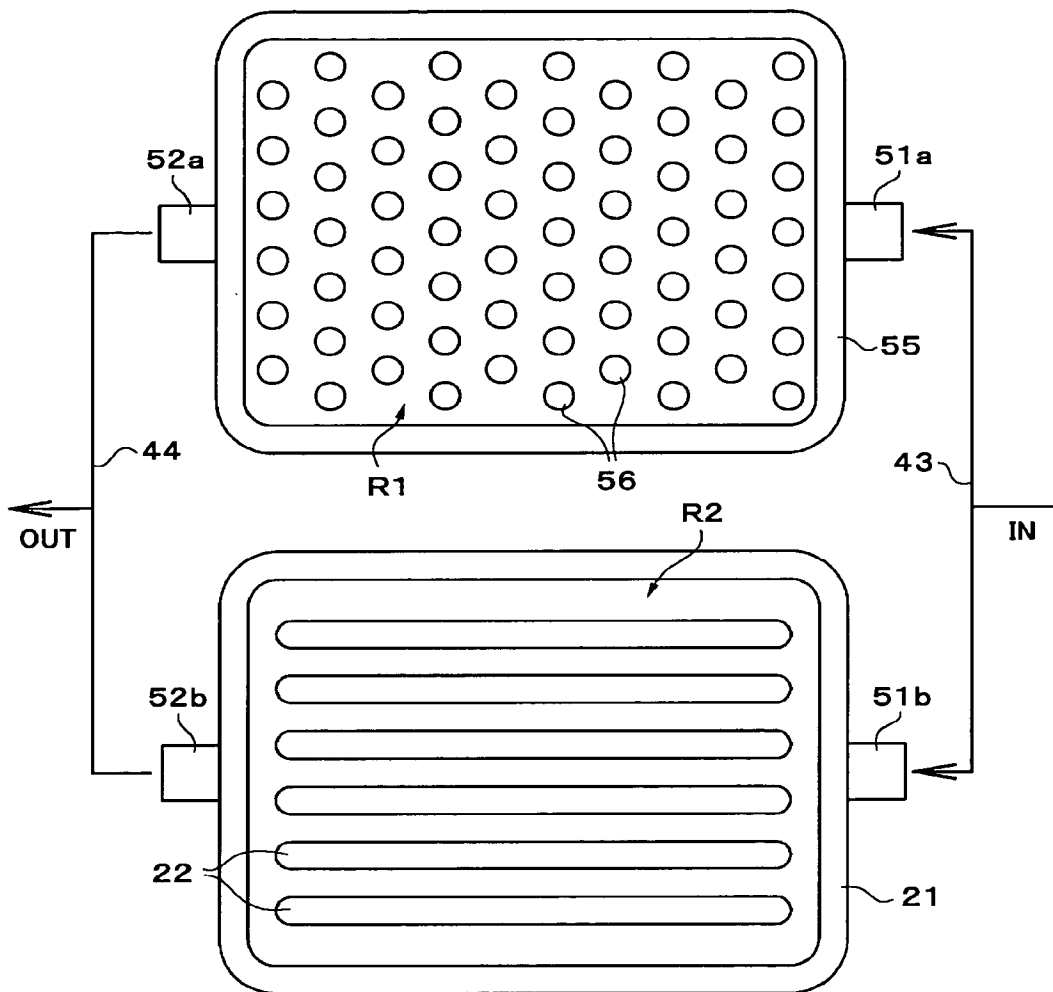
FIG. 13



Appendix A

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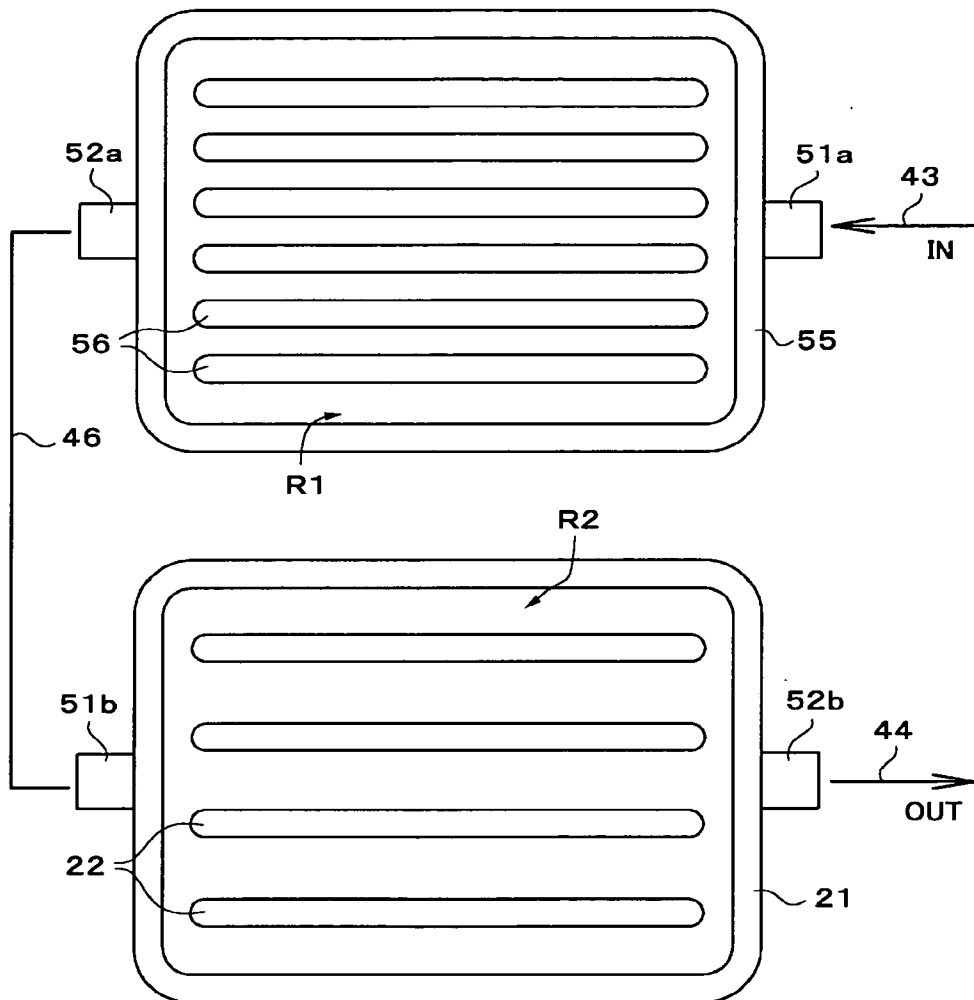
FIG. 14



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FIG. 15

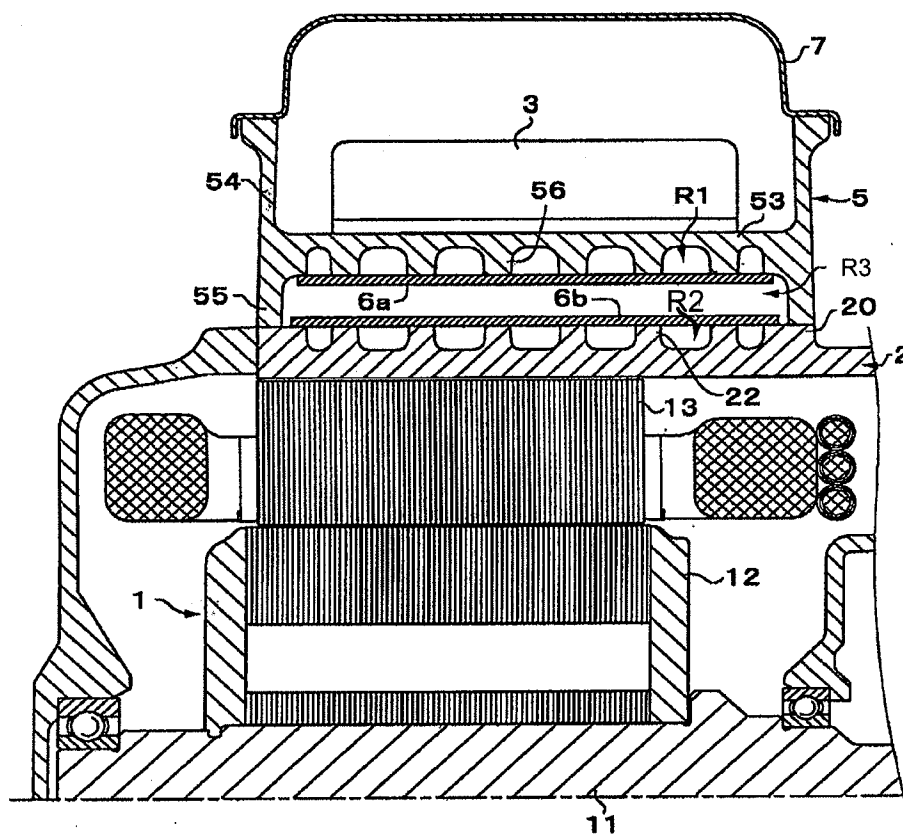


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Replacement Sheet

FIG. 16



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FIG. 17

